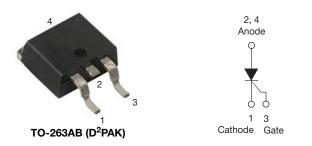
Vishay Semiconductors

Thyristor Surface Mount Phase Control SCR, 16 A



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PRODUCT SUMMARY					
Package	TO-263AB (D ² PAK)				
Diode variation	Single SCR				
I _{T(AV)}	10 A				
V _{DRM} /V _{RRM}	1600 V				
V _{TM}	1.4 V				
I _{GT}	60 mA				
TJ	-40 °C to 125 °C				

FEATURES

• Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C



- Designed and qualified according JEDEC[®]-JESD 47
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

APPLICATIONS

- Input rectification (soft start)
- Vishay input diodes, switches and output rectifiers which are in identical package outlines

DESCRIPTION

The VS-16TTS16SPbF high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS						
APPLICATIONS SINGLE-PHASE BRIDGE THREE-PHASE BRIDGE UNITS						
NEMA FR-4 or G-10 glass fabric-based epoxy with 4 oz. (140 μm) copper	2.5	3.5				
Aluminum IMS, R _{thCA} = 15 °C/W	6.3	9.5	A			
Aluminum IMS with heatsink, $R_{thCA} = 5 \text{ °C/W}$	14.0	18.5				

Note

• $T_A = 55 \ ^\circ C$, $T_J = 125 \ ^\circ C$, footprint 300 mm²

MAJOR RATINGS AND CHARACTERISTICS					
SYMBOL	CHARACTERISTICS VALUES		UNITS		
I _{T(AV)}	Sinusoidal waveform	10	•		
I _{RMS}		16	A		
V _{RRM} /V _{DRM}		1600	V		
I _{TSM}		200	A		
V _T	10 A, T _J = 25 °C	1.4	V		
dV/dt		500	V/µs		
dl/dt		150	A/µs		
TJ		-40 to 125	°C		

VOLTAGE RATINGS						
PART NUMBER	V _{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I _{RRM} /I _{DRM} AT 125 °C mA			
VS-16TTS16SPbF	1600	1600	10			

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ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEAT CONDITIONS		VALUES			
FANAMETEN	STMDUL	TEST CONDITIONS	TYP.	MAX.	UNITS		
Maximum average on-state current	I _{T(AV)}	T_{C} = 93 °C, 180° conduction, half sine wave	10				
Maximum RMS on-state current	I _{RMS}		1	6	А		
Maximum peak, one-cycle,	1	10 ms sine pulse, rated V _{RRM} applied	17	70	A		
non-repetitive surge current	I _{TSM}	10 ms sine pulse, no voltage reapplied	20	00			
Maximum I ² t for fusing	l ² t	10 ms sine pulse, rated V _{RRM} applied	14	14	A ² s		
Maximum -t for fusing	1-1	10 ms sine pulse, no voltage reapplied		200			
Maximum I²√t for fusing	l²√t	t = 0.1 ms to 10 ms, no voltage reapplied	2000		A²√s		
Maximum on-state voltage drop	V _{TM}	10 A, T _J = 25 °C	1.4		V		
On-state slope resistance	r _t			24.0		1.0	mΩ
Threshold voltage	V _{T(TO)}	T _J = 125 °C		.1	V		
Maximum reverse and direct looks as aurent	1 /1	$T_J = 25 \text{ °C}$	0	.5			
Maximum reverse and direct leakage current	I _{RM} /I _{DM}	I_{DM} $T_J = 125 °C$ $V_R = Rated V_{RRM}/V_{DRM}$		0			
Holding current	Ι _Η	Anode supply = 6 V, resistive load, initial I_T = 1 A, T_J = 25 °C		150	mA		
Maximum latching current	١L	Anode supply = 6 V, resistive load, $T_J = 25 \degree C$		Anode supply = 6 V, resistive load, T_J = 25 °C		00	
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J max.$ linear to 80 % $V_{DRM} = Rg - k = Open$ 500		00	V/µs		
Maximum rate of rise of turned-on current	dl/dt		150		A/µs		

TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum peak gate power	P _{GM}		8.0	W	
Maximum average gate power	P _{G(AV)}		2.0	vv	
Maximum peak positive gate current	+ I _{GM}		1.5	А	
Maximum peak negative gate voltage	- V _{GM}		10	V	
	I _{GT}	Anode supply = 6 V, resistive load, T_J = - 10 °C	90		
Maximum required DC gate current to trigger		Anode supply = 6 V, resistive load, T_J = 25 °C	60	mA	
		Anode supply = 6 V, resistive load, T_J = 125 °C	35		
		Anode supply = 6 V, resistive load, T_J = - 10 °C	3.0		
Maximum required DC gate voltage to trigger	V _{GT}	Anode supply = 6 V, resistive load, T_J = 25 °C	2.0	V	
voltage to trigger		Anode supply = 6 V, resistive load, T_J = 125 °C	1.0	V	
Maximum DC gate voltage not to trigger	V _{GD}		0.25		
Maximum DC gate current not to trigger	I _{GD}	$T_{J} = 125 \text{ °C, } V_{DRM} = \text{Rated value} $ 2.0		mA	

SWITCHING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Typical turn-on time	t _{gt}	T _J = 25 °C	0.9		
Typical reverse recovery time	t _{rr}	T _{.1} = 125 °C	4	μs	
Typical turn-off time	tq	1J = 125 C	110		

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VS-16TTS16SPbF Series



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THERMAL - MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum junction and storage temperature range	T _J , T _{Stg}	TJ, TStg For 10 s (1.6 mm from case)		°C	
Soldering temperature	T _S				
Maximum thermal resistance, junction to case	R _{thJC}	R _{thJC} DC operation		°C/W	
Typical thermal resistance, junction to ambient	R _{thJA}	PCB mount ⁽¹⁾	40	0/10	
Approximate weight			2	g	
			0.07	oz.	
Marking device		Case style D ² PAK (SMD-220)	16TTS	16S	

Note

⁽¹⁾ When mounted on 1" square (650 mm²) PCB of FR-4 or G-10 material 4 oz. (140 μm) copper 40 °C/W.

For recommended footprint and soldering techniques refer to application note #AN-994.

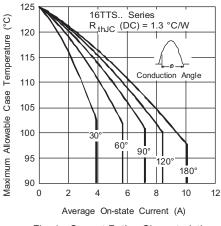


Fig. 1 - Current Rating Characteristics

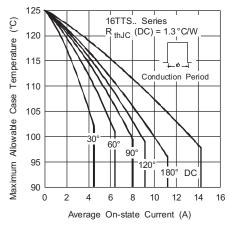


Fig. 2 - Current Rating Characteristics

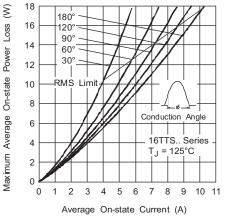


Fig. 3 - On-State Power Loss Characteristics

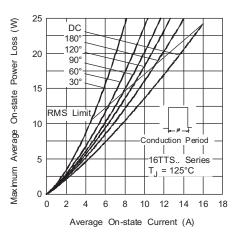


Fig. 4 - On-State Power Loss Characteristics

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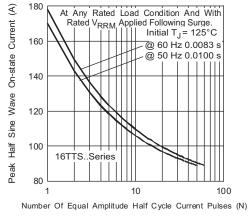
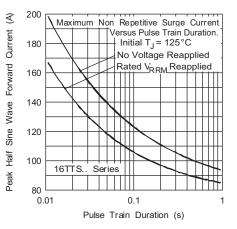
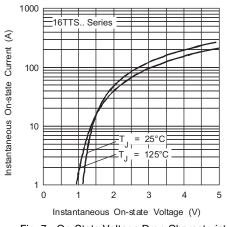
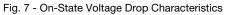


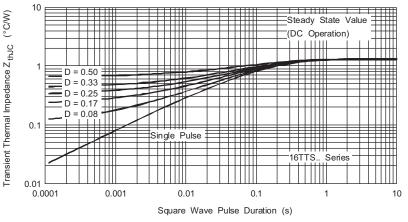
Fig. 5 - Maximum Non-Repetitive Surge Current









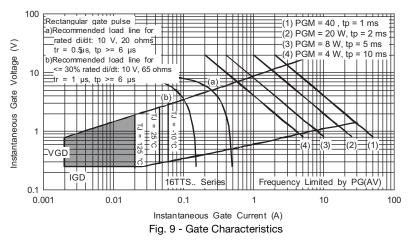




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VS-16TTS16SPbF Series

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ORDERING INFORMATION TABLE

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SHA

Device code	VS-	16	т	т	S	16	S	TRL	PbF
	1	2	3	4	5	6	7	8	9
	1 -		-	niconduc	ctors pro	oduct			
			Current rating Circuit configuration:						
	4		T = single thyristor Package:						
	5.	-	T = TO-220AC Type of silicon:						
	_	S =	S = standard recovery rectifier						
	6		Voltage rating: Voltage code x $100 = V_{RRM} (16 = 1600 \text{ V})$						
	7 · 8 ·		S = TO-220 D ² PAK (SMD-220) version • None = tube						
				e and re	el (left o	oriented)		
				be and re	`		,		
	9	- PbF	= lead	(Pb)-fre	е				

ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-16TTS16SPbF	50	1000	Antistatic plastic tubes				
VS-16TTS16STRRPbF	800	800	13" diameter reel				
VS-16TTS16STRLPbF	800	800	13" diameter reel				

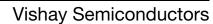
LINKS TO RELATED DOCUMENTS				
Dimensions www.vishay.com/doc?95046				
Part marking information	www.vishay.com/doc?95054			
Packaging information	www.vishay.com/doc?95032			

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Outline Dimensions

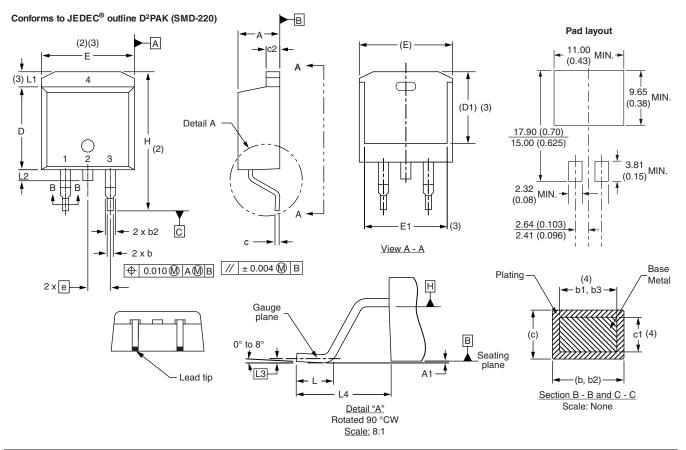


D²PAK

DIMENSIONS in millimeters and inches

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ISHA



SYMBOL	MILLIMETERS		INCHES		NOTES	SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.	NOTES	STINDUL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.06	4.83	0.160	0.190		D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010		E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039		E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4	е	2.54 BSC		0.100 BSC		
b2	1.14	1.78	0.045	0.070		Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4	L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029		L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4	L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065		L3	0.25 BSC		0.010 BSC		
D	8.51	9.65	0.335	0.380	2	L4	4.78	5.28	0.188	0.208	

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5 M-1994

⁽²⁾ Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

⁽³⁾ Thermal pad contour optional within dimension E, L1, D1 and E1

(4) Dimension b1 and c1 apply to base metal only

⁽⁵⁾ Datum A and B to be determined at datum plane H

⁽⁶⁾ Controlling dimension: inch

⁽⁷⁾ Outline conforms to JEDEC[®] outline TO-263AB

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